

Serial No. 09/493,819
Docket No. T36-119817M/KOH

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Please amend claims 1, 3, 5, and 6 as follows:

1. (Three Times Amended) A group III nitride compound semiconductor device of a successively laminated structure, comprising:

a substrate;

a buffer layer formed directly on said substrate;

[a first] an intervening layer formed [of] directly on said buffer layer, said intervening layer comprising $In_xGa_{1-x}N$, where [$0 < X < 1$]; and

a [second] light-emitting layer formed [of] directly on said intervening layer, said light-emitting layer comprising $In_yGa_{1-y}N$, where [$0 < Y < 1$, $Y \neq X$];

wherein a first In composition ratio of [In in] said [first] intervening layer, X, changes from a first interface with said buffer layer to a second interface with said light-emitting layer, such that, said first In composition ratio, X, at said second interface becomes substantially equal [is changed continuously or intermittently in a direction toward the second layer side from the buffer layer side so that a composition of said first layer in a face brought into contact with said second layer becomes substantially equal] to a second In composition ratio, Y, of said [second] light-emitting layer[; and

wherein said buffer layer is disposed between and in direct contact with both said substrate and said first layer, and said first layer is disposed between and in direct contact with both said buffer layer and said second layer].

3. (Three Times Amended) A group III nitride compound semiconductor device of a successively laminated structure, comprising:

a substrate;

a buffer layer formed directly on said substrate and having a buffer layer lattice constant;

[a first] an intervening layer formed [of] directly on said buffer layer, said intervening layer comprising $Al_aGa_bIn_{1-a-b}N$, where [$0 < a < 1$, $0 < b < 1$, and $a+b < 1$]; and

a [second] light-emitting layer formed [of] directly on said intervening layer,

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said light-emitting layer comprising In_xGa_{1-x}N, where [(0<Y<1)], and having a second layer lattice constant,

wherein [said buffer layer is disposed between and in direct contact with both said substrate and said first layer, and said first layer is disposed between and in direct contact with both said buffer layer and said second layer, and

wherein a] composition [ratio] ratios of at least Al and In [in] of said [first] intervening layer [is changed continuously or intermittently in a direction toward the second layer side from the buffer layer side so] change from a first interface with said buffer layer to a second interface with said light-emitting layer, such that, a first lattice constant of said [first] intervening layer [in a face brought into contact with said second layer becomes substantially equal] at said first interface changes to a second lattice constant that is substantially equal to a lattice constant of said [second] light-emitting layer.

5. (Amended) A group III nitride compound semiconductor device according to claim 3, wherein [a] said composition [ratio] ratios of at least Al and In [in] of said [first] intervening layer [is changed] change continuously or intermittently in a direction toward [the second] said light-emitting layer [side] from [the] said first interface with said buffer layer [side], so that, a band gap at said second interface of said [first] intervening layer [in the face brought into contact with said second layer becomes] is wider than a band gap of said [second] light-emitting layer.

6. (Twice Amended) A group III nitride compound semiconductor device according to claim 3, wherein [the] said composition ratio of at least Al [and In in] of said [first] intervening layer is changed continuously or intermittently in the direction toward [the second] said light-emitting layer [side] from [the] said first interface with said buffer layer [side], so that, a band gap at said second interface of said [first] intervening layer [in a face brought into contact with said second layer becomes] is wider than a band gap of said second layer.